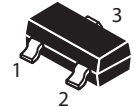
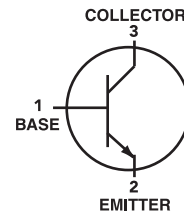


### NPN General Purpose Transistors

 Lead(Pb)-Free



SOT-23

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector-Base Voltage	$V_{CBO}$	60	Vdc
Emitter-Base Voltage	$V_{EBO}$	7.0	Vdc
Collector Current-Continuous	$I_C$	150	mAdc

#### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A=25^{\circ}\text{C}$	$P_D$	200	mW
Derate above $25^{\circ}\text{C}$		1.6	$\text{mW}/^{\circ}\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^{\circ}\text{C}/\text{W}$
Junction and Storage, Temperature	$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$

#### DEVICE MARKING

2SC2412KQ=G1F, 2SC2412KR=G2F, 2SC2412KS=G3F

#### ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C=1.0\text{mA}, I_B=0$ )	$V_{(BR)CEO}$	50	-	Vdc
Collector-Base Breakdown Voltage ( $I_C=50\mu\text{A}, I_E=0$ )	$V_{(BR)CBO}$	60	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E=50\mu\text{A}, I_C=0$ )	$V_{(BR)EBO}$	7.0	-	Vdc
Collector Cutoff Current ( $V_{CE}=50\text{Vdc}, I_E=0$ )	$I_{CEO}$	-	0.1	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CB}=60\text{Vdc}, I_E=0$ )	$I_{CBO}$	-	0.1	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB}=7.0\text{Vdc}, I_C=0$ )	$I_{EBO}$	-	0.1	$\mu\text{Adc}$

1.FR-5=1.0 x 0.75 x 0.062 in

# 2SC2412K



## ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Typ	Max	Unit
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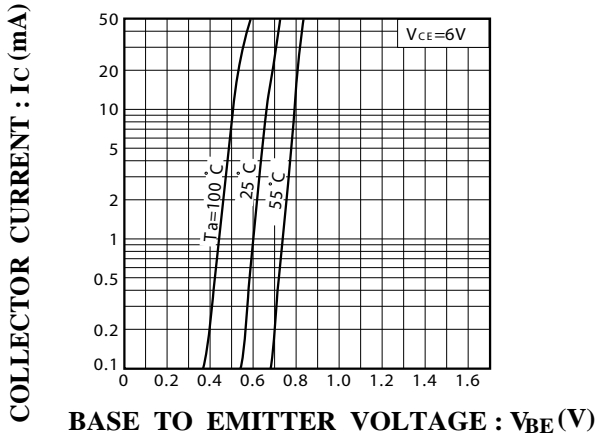
### ON CHARACTERISTICS

DC Current Gain ( $I_C=1\text{ mAdc}, V_{CE}=6.0\text{ Vdc}$ )	$h_{FE}$	120	-	560	-
Collector-Emitter Saturation Voltage ( $I_C=50\text{ mAdc}, I_B=5\text{ mAdc}$ )	$V_{CE(sat)}$	-	-	0.4	Vdc
Output Capacitance $V_{CE}=12\text{ Vdc}, I_E=0\text{ A}, f=1\text{ MHz}$	$C_{ob}$	-	2.0	3.5	PF
Current-Gain-Bandwidth Product ( $I_E=2\text{ mAdc}, V_{CE}=12\text{ Vdc}, f=100\text{ MHz}$ )	$f_T$	-	180	-	MHz

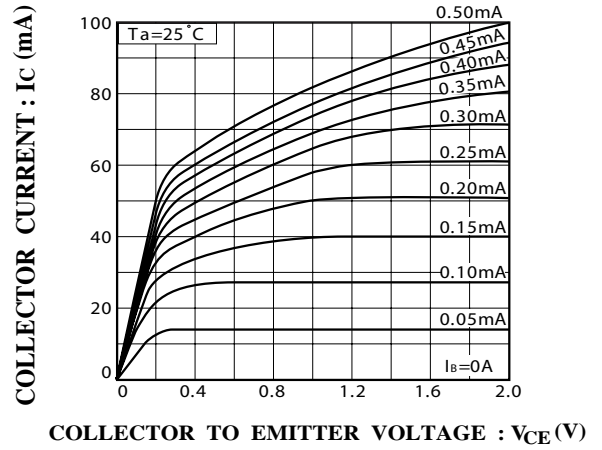
### CLASSIFICATION OF $h_{FE}$

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	G1F	G2F	G3F

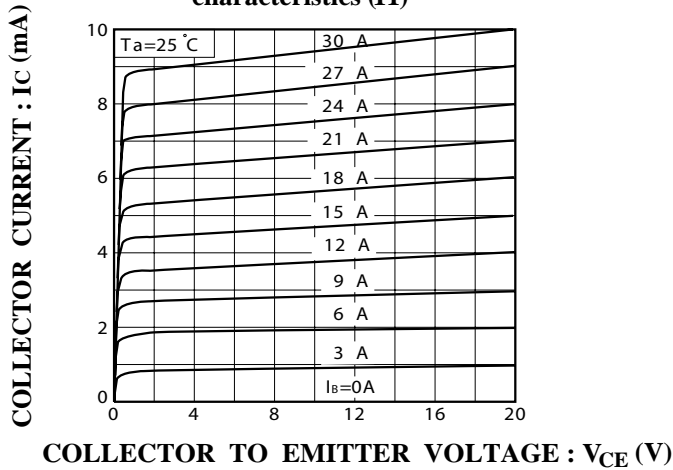
**Fig.1** Grounded emitter propagation characteristics



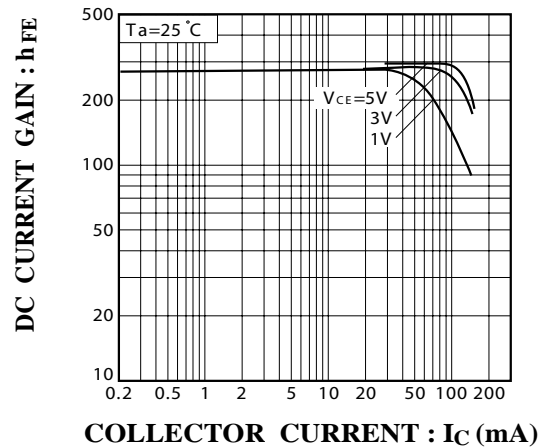
**Fig.2** Grounded emitter output characteristics (I)



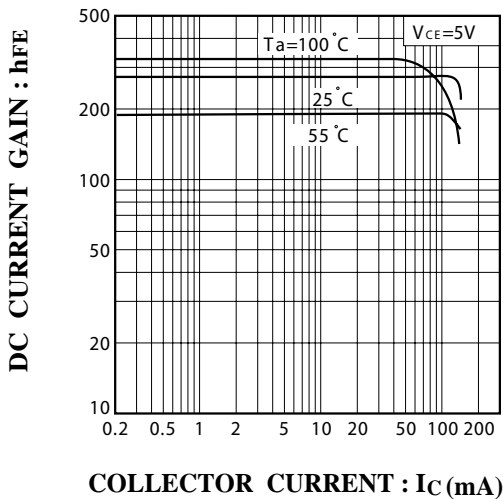
**Fig.3** Grounded emitter output characteristics (II)



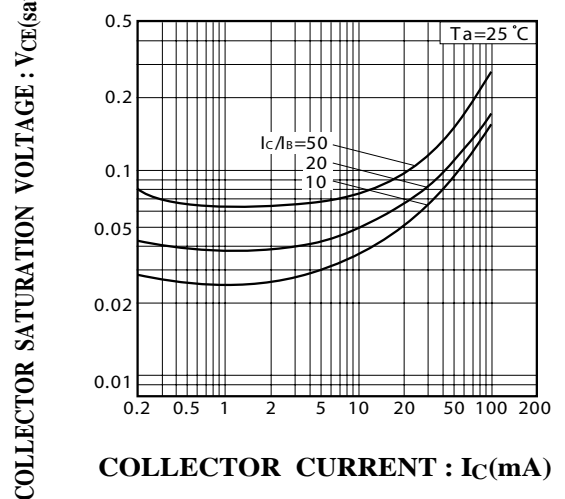
**Fig.4** DC current gain vs. collector current (I)



**Fig.5** DC current gain vs. collector current (II)

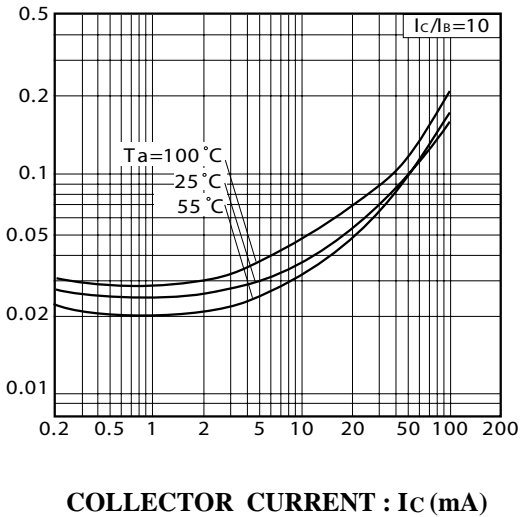


**Fig. 6** Collector-emitter saturation voltage vs. collector current



COLLECTOR SATURATION VOLTAGE :  $V_{CE(sat)}$  (V)

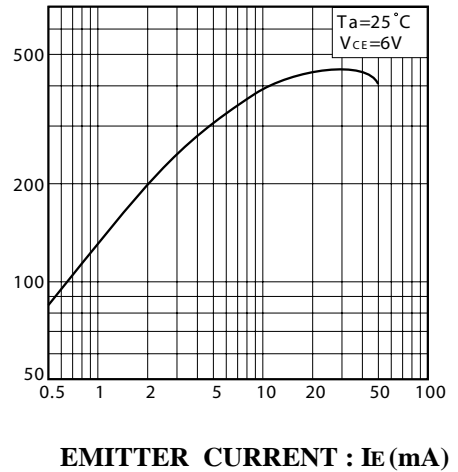
**Fig.7 Collector-emitter saturation voltage vs. collector current (1)**



COLLECTOR CURRENT :  $I_C$  (mA)

TRANSITION FREQUENCY :  $f_T$  (MHz)

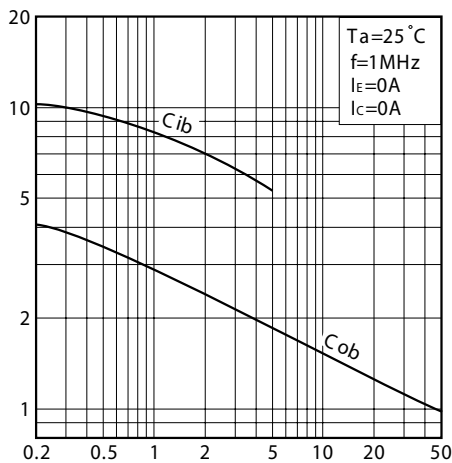
**Fig.8 Gain bandwidth product vs. emitter current**



EMITTER CURRENT :  $I_E$  (mA)

**Fig.9 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage**

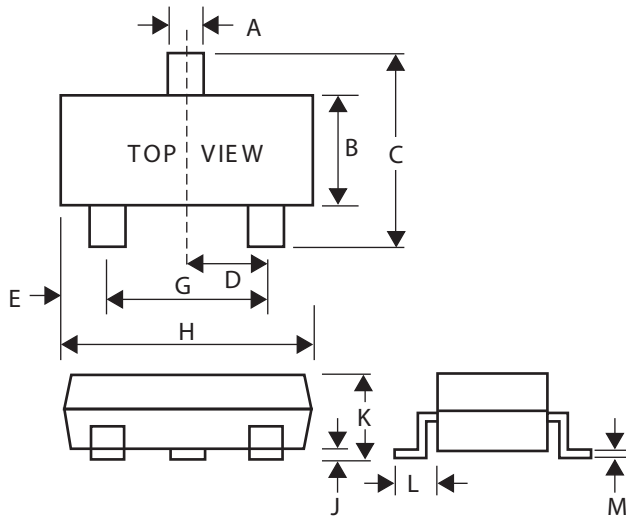
COLLECTOR OUTPUT CAPACITANCE :  $C_{ob}$  (pF)  
EMITTER INPUT CAPACITANCE :  $C_{ib}$  (pF)



COLLECTOR TO BASE VOLTAGE :  $V_{CB}$  (V)  
EMITTER TO BASE VOLTAGE :  $V_{EB}$  (V)

## SOT-23 Package Outline Dimensions

Unit:mm



Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25